

900V N-Channel MOSFET

Description

The MS14N60 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220 package is universally preferred for all commercial-industrial applications

Features

- · Low On Resistance
- · Simple Drive Requirement
- · Low Gate Charge
- · Fast Switching Characteristic
- RoHS compliant package

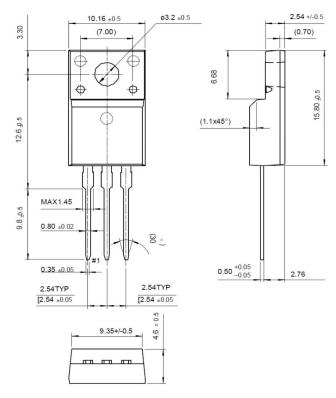
Application

- Adapter
- · Switching Mode Power Supply

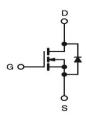
Packing & Order Information

50/Tube; 1,000/Box





Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings						
Symbol	Parameter	Value	Unit			
V_{DSS}	Drain-Source Voltage	600	V			
V _{GS}	Gate-Source Voltage	±30	V			
	Drain Current -Continuous (TC=25°C)	14	А			
I _D	Drain Current -Continuous (TC=100°C)	8.4	A			
I _{DM}	Drain Current -Pulsed	56	А			
I _{AR}	Avalanche Current	14	А			
E _{AS}	Single Pulsed Avalanche Energy	53	mJ			
E _{AR}	Repetitive Avalanche Energy	16	mJ			
dV/dt	Peak Diode Recovery dV/dt	4.5	V/ns			
TJ	Storage Temperature	150	°C			
P _D	Power Dissipation (TC=25°C)	60	W			
	Derate above 25C	0.35	W/°C			

[•] Drain current limited by maximum junction temperature



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Absolute Maximum Ratings (Tc=25°C unless otherwise specified)						
Symbol	Parameter	Value	Unit			
T _{STG}	Operating Junction and Storage Temperature	-55 to +150	°C			
T _L	Maximum lead temperature for soldering purposes,	300	°C			
	1/8" from case for 5 seconds	300				

Note:

- 1. Repetitive rating; pulse width limited by maximum junction temperature.
- 2. I_{AS} =14A, V_{DD} =50V, L=0.5mH, R_{G} =25 Ω , starting TJ=+25°C.
- 3. $I_{SD} \le 7.5A$, $dI/dt \le 100A/\mu s$, $VDD \le BVDSS$, starting TJ = +25°C.

Thermal Characteristics						
Symbol	Parameter	Тур.	Max.	Units		
$R_{\theta JC}$	Thermal Resistance , Junction-to-Case		2.58	°C/W		
$R_{\theta JA}$	Thermal Resistance , Junction-to-Ambient		62.5	C/VV		

Static Characteristics							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu \text{A}$	600			V	
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C		0.7		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V , V _{GS} = 0 V V _{DS} = 480 V , T _C = 125°C			1 10	uA	
I _{GSS}	Gate-Body Leakage Current, Forward	V _{DS} = ±30			±100	nA	
*R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10 V , I _D = 8.4 A			0.55	Ω	

Dynamic Characteristics							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
C_{ISS}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f=1.0 \text{MHz}$		2222		pF	
Coss	Output Capacitance			180		pF	
C _{RSS}	Reverse Transfer Capacitance			17		pF	
t _{d(on)}	Turn-On Time			16		ns	
t _r	Turn-On Time	$V_{DD} = 250 \text{ V}, I_{D} = 14 \text{ A},$ $V_{GS} = 10 \text{ V}, R_{G} = 9.1 \Omega$		30		ns	
t _{d(off)}	Turn-Off Delay Time			48		ns	
tf	Turn-Off Fall Time			34		ns	



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Dynamic Characteristics							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
Q_g	Total Gate Charge	$V_{DD} = 250 \text{ V}, I_{D} = 14 \text{ A},$ $V_{GS} = 10 \text{ V}$		40		nC	
Q_{gs}	Gate-Source Charge			10		nC	
Q_{gd}	Gate-Drain Charge			15		nC	

Source-Drain Diode							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
Is		$V_D = V_G = 0$,			14		
I _{SM}		$V_D = V_G = 0,$ $V_S = 1.3 \text{ V}$			56	A	
V _{SD}		I _S = 14 A , V _{GS} = 0 V			1.5	V	
t _{rr}		I _S =14 A , V _{GS} = 0 V		393		ns	
Q _{rr}		diF/dt=100A/µs		3529		μC	

^{*}Pulse Test : Pulse Width ≤300µs, Duty Cycle≤2%



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